

SILICON DIFFUSED TYPE FAST RECOVERY DIODE

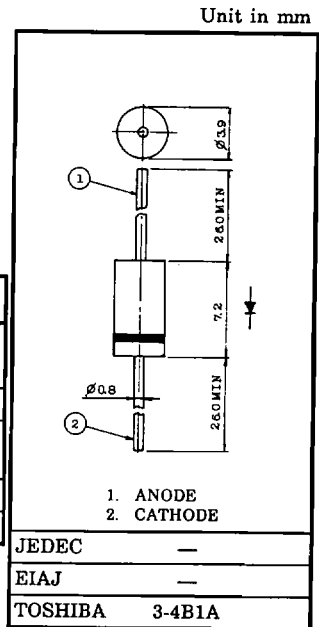
TVR4J/N

○ HIGH SPEED RECTIFIER APPLICATIONS. (FAST RECOVERY)

- Repetitive Peak Reverse Voltage : $V_{RRM}=600, 1000V$
- Average Forward Current : $I_F(AV) = 1.2A (T_a=55^\circ C)$
- Reverse Recovery Time : $t_{rr}=20\mu s$

MAXIMUM RATING

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	TVR4J	600	V
	TVR4N	1000	
Average Forward Current	$I_F(AV)$	1.2	A
Peak One Cycle Surge Forward Current (Non Repetitive)	I_{FSM}	100 (50Hz)	A
Junction Temperature	T_j	-40~150	°C
Storage Temperature Range	T_{stg}	-40~150	°C



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

Weight : 0.47g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	V_{FM}	$I_{FM}=5A$	—	—	1.2	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM}=\text{Rated}$	—	—	10	μA
Reverse Recovery Time	t_{rr}	$I_F=20mA, I_R=1mA$	—	—	20	μs
Thermal Resistance (Junction to Ambient)	$R_{th(j-a)}$	DC	—	—	80	°C/W

MARKING

